

NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

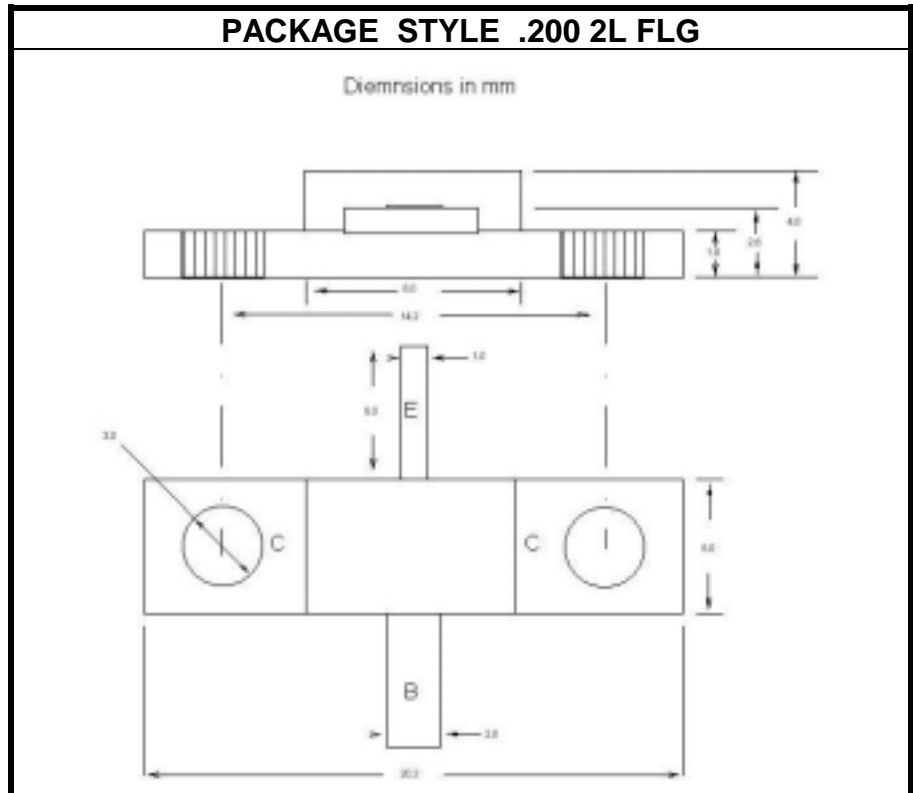
The **ASI 2SC2951** is a High Frequency Transistor Designed for General Purpose Oscillator Applications up to 10 GHz.

FEATURES:

- $P_{osc} = 630 \text{ mW}$ Typical at 7.5 GHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	440 mA
V_{CE}	16 V
V_{CB}	25 V
P_{DISS}	9.7 W @ $T_C = 25 \text{ }^\circ\text{C}$
T_J	-65 to +200 $^\circ\text{C}$
T_{STG}	-65 to +200 $^\circ\text{C}$
θ_{JC}	18 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25 \text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 1.0 \text{ mA}$			16			V
BV_{CBO}	$I_C = 100 \text{ } \mu\text{A}$			25			V
BV_{EBO}	$I_E = 100 \text{ } \mu\text{A}$			1.5			V
I_{CBO}	$V_{CB} = 15 \text{ V}$					1.0	μA
I_{EBO}	$V_{EB} = 1.0 \text{ V}$					4.0	μA
h_{FE}	$V_{CE} = 8.0 \text{ V}$	$I_C = 200 \text{ mA}$		20		200	---
C_{OB}	$V_{CB} = 10 \text{ V}$	$f = 1.0 \text{ MHz}$			2.9	4.0	pF
$ S_{21} ^2$	$V_{CC} = 8.0 \text{ V}$	$I_C = 200 \text{ mA}$	$f = 1.0 \text{ GHz}$	3.5			dB
P_{osc}	$V_{CE} = 12 \text{ V}$	$I_C = 200 \text{ mA}$	$f = 7.5 \text{ GHz}$		630		mW